

SEMICONDUCTOR INTEGRATED CIRCUIT DEVICE HAVING A LEAKAGE  
CURRENT CUTOFF CIRCUIT, CONSTRUCTED USING MT-CMOS, FOR  
REDUCING STANDBY LEAKAGE CURRENT

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ABSTRACT OF THE DISCLOSURE

10           A semiconductor integrated circuit device has a  
high-threshold N-channel type MIS field effect transistor  
and a load circuit. The high-threshold N-channel type  
MIS field effect transistor is connected between a real  
high-potential power supply line and a pseudo high-  
15           potential power supply line. The load circuit has a low-  
threshold P-channel type MIS field effect transistor and  
a low-threshold N-channel type MIS field effect  
transistor. A first power supply terminal of the load  
circuit is connected to the pseudo high-potential power  
20           supply line, and a second power supply terminal of the  
load circuit is connected to a real low-potential power  
supply line.